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46. J.B. Philipp, J. Klein, C. Recher, T. Walther, W. Mader, M. Schmid, R. Suryanarayanan, L. Alff and R. Gross: Microstructure and magnetoresistance of epitaxial films of the layered perovskite $La_{2-2x}Sr_{1+2x}Mn_2O_7$ ($x=0.3$ and 0.4), Phys. Rev. B 65 (2002) 184411.1-11


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E extended abstracts of one page or two pages (partially refereed)


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